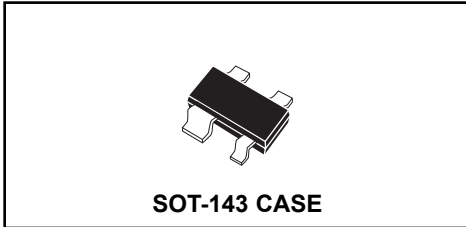


CMFD2004i
DUAL ISOLATED HIGH VOLTAGE SWITCHING DIODE



CentralTM

Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMFD2004i type is a Silicon Dual Isolated High Voltage Switching diode designed for surface mount switching applications requiring high voltage capabilities.

MARKING CODE: CJP

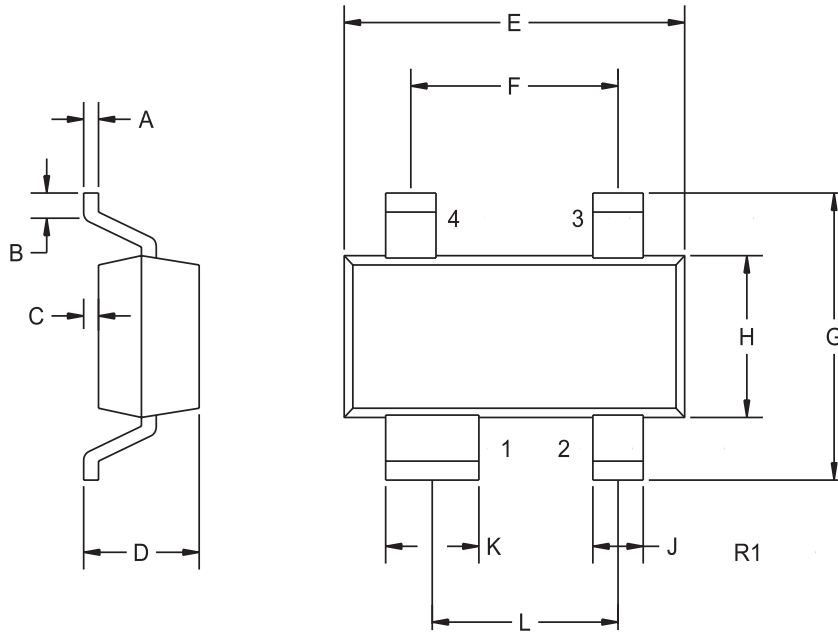
MAXIMUM RATINGS: ($T_A=25\text{ }^\circ\text{C}$)

	SYMBOL		UNITS
Continuos Reverse Voltage	V_R	240	V
Peak Repetitive Reverse Voltage	V_{RRM}	300	V
Peak Repetitive Reverse Current	I_O	200	mA
Continuous Forward Current	I_F	225	mA
Peak Repetitive Forward Current	I_{FRM}	625	mA
Forward Surge Current, $t_p=1\mu\text{s}$	I_{FSM}	4.0	A
Forward Surge Current, $t_p=1\text{s}$	I_{FSM}	1.0	A
Power Dissipation	P_D	350	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	Θ_{JA}	357	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25\text{ }^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=240\text{V}$		100	nA
I_R	$V_R=240\text{V}, T_A=150\text{ }^\circ\text{C}$		100	μA
BV_R	$I_R=100\text{ }\mu\text{A}$	300		V
V_F	$I_F=100\text{mA}$		1.0	V
C_T	$V_R=0\text{V}, f=1.0\text{MHz}$		5.0	pF
t_{rr}	$I_F=I_R=30\text{mA}, I_{rr}=3.0\text{mA}, R_L=100\Omega$		50	ns

SOT-143 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) CATHODE 1
- 2) CATHODE 2
- 3) ANODE 2
- 4) ANODE 1

MARKING CODE: CJP

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.005	0.10	0.13
B	0.006	-	0.15	-
C	0.003	0.005	0.08	0.13
D	0.037	0.043	0.94	1.09
E	0.110	0.118	2.79	3.00
F	0.079		2.01	
G	-	0.098	-	2.49
H	0.047	0.051	1.19	1.30
J	0.014	0.018	0.36	0.46
K	0.030	0.033	0.76	0.84
L	0.071		1.80	

SOT-143 (REV: R1)